COMPLIANT



Vishay Semiconductors

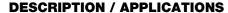
HEXFRED® Ultrafast Soft Recovery Diode, 140 A



PRIMARY CHARACTERISTICS					
V_{R}	1200 V				
V _F (typical)	2.8 V				
t _{rr} (typical)	48 ns				
I _{F(DC)} at T _C , per module	140 A at 74 °C				
I _{F(AV)} at T _C , per module	140 A at 46 °C				
Package	SOT-227				

FEATURES

- · Fast recovery time characteristic
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and qualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



The dual diode series configuration VS-HFA140FA120 is used for output rectification or freewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	V_R		1200	V
Continuous forward current per leg	H I _E I T _C = 74 °C ⊢	70		
per module		1 _C = 74	140	Α
Single pulse forward current	I _{FSM}	T _J = 25 °C	350	
Maximum power dissination, per lea	P _D	T _C = 25 °C	357	W
Maximum power dissipation, per leg		T _C = 100 °C	143]
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 minute	2500	V
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-	
		I _F = 60 A	-	2.8	4.0	
Forward voltage, per leg		I _F = 120 A	-	3.6	5.3	V
	V_{FM}	I _F = 60 A, T _J = 125 °C	-	2.7	-	
		I _F = 60 A, T _J = 150 °C	-	2.65	-	
		$V_R = V_R$ rated	-	2.0	75	μΑ
Reverse leakage current, per leg	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	1.6	5	mA
		T _J = 150 °C, V _R = V _R rated	-	5	10] ""A



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	l ₁		I _F = 1 A; dI _F /dt = 200 A/µs; V _R = 30 V		48	i	
Reverse recovery time, per leg	t _{rr}	T _J = 25 °C		ı	145	-	ns
		T _J = 125 °C		-	218	-	
Peak recovery current, per leg		T _J = 25 °C	I _F = 50 A dI _F /dt = - 200 A/μs	=	13	-	Α
Feak recovery current, per leg	IRRM	T _J = 125 °C	$V_{R} = 200 \text{ V}$	=	18	-	A
Poverse receivery charge per les	Q _{rr}	T _J = 25 °C		=	910	-	nC
Reverse recovery charge, per leg		T _J = 125 °C		-	1920	=	
Junction capacitance, per leg	C _T	V _R = 1200 V		=	27	-	pF

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	В		-	-	0.35	
Junction to case, both legs conducting	R _{thJC}		-	-	0.175	°C/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.05	-]
Weight			-	30	-	g
Mounting toyang		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				S	OT-227	

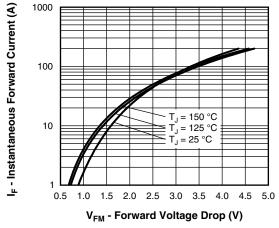


Fig. 1 - Typical Forward Voltage Drop Characteristics

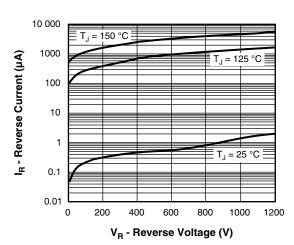


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

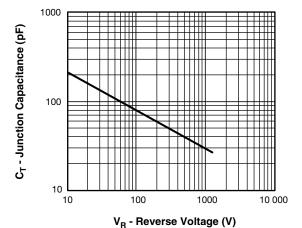


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



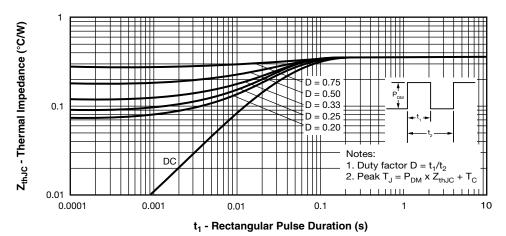


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

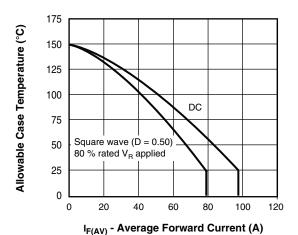


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

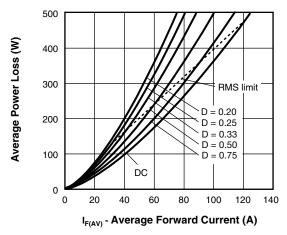


Fig. 6 - Forward Power Loss Characteristics

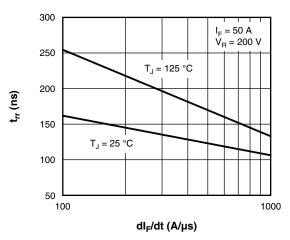


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

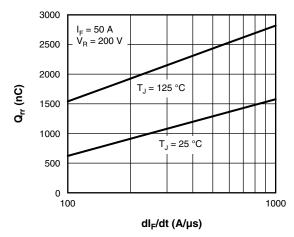


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

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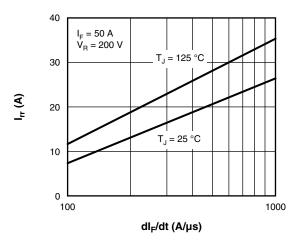


Fig. 9 - Typical Peak Recovery Current vs. dl_F/dt

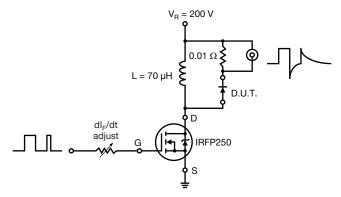
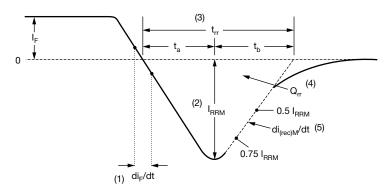


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di_F/dt rate of change of current through zero crossing
- (2) $\boldsymbol{I}_{\text{RRM}}$ peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{rr}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \boldsymbol{Q}_{rr} area under curve defined by \boldsymbol{t}_{rr} and \boldsymbol{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

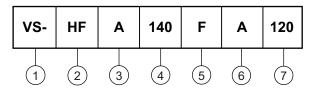
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 HEXFRED® family
- Process designator (A = electron irradiated)
- 4 Average current (140 = 140 A)
- 5 Circuit configuration (two separate diodes, parallel pin-out)
- 6 Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (120 = 1200 V)

CIRCUIT CONFIGURATION					
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
Two separate diodes, parallel pin-out	F	Lead Assignment 4 0 0 3 4 1 0 0 2 1			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95423				
Part marking information	www.vishay.com/doc?95425				



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